



[10191/955]

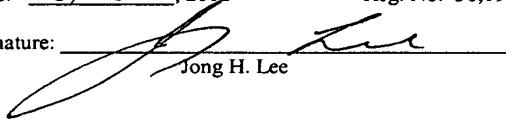
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Inventor(s) : Joerg SCHAEFER et al.  
Serial No. : 09/238,262  
Filed : January 27, 1999  
For : METHOD OF PRODUCING STRUCTURED WAFERS  
Examiner : Anita Karen Alanko  
Art Unit : 1746

Assistant Commissioner for  
Patents  
Washington, D.C. 20231

I hereby certify that this correspondence is being deposited with the  
United States Postal Service as first class mail in an envelope addressed  
to: Assistant Commissioner for Patents, Washington, D.C. 20231 on

Date: 8/15, 2002 Reg. No. 36,197

Signature: 

Jong H. Lee

AMENDMENT

SIR:

In response to the Office Action dated April 10, 2002, kindly amend the above-identified application before examination, as set forth below.

IN THE SPECIFICATION:

please replace the paragraph beginning on page 2, line 7, with the following paragraph:

Figure 1 shows a first embodiment of the method according to the present invention as a two-sided one-step etching process. Part 1 shows a cross-sectional view of wafer 20, which made be made of a single material, with a front side 22, a back side 23 and an edge area 21. The wafer is shown only partially, continuing toward the left, where it is delimited by another edge area (not shown). A nitride layer is applied to the wafer by gas phase deposition. Then the nitride layer is structured by a conventional photoresist technique, with the resist being applied to the nitride layer, exposed selectively and then developed; (when using a positive resist) the exposed part of the resist is next removed, then the exposed part of the

NY01 471501v1

RECEIVED  
AUG 15 2002  
TO 700

COPY OF PAPERS  
ORIGINALLY FILED